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N.W.H. tener
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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

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TECHNOLOGY CENTER 2800

Subject:

Serial No. 09/325,951 ✓ 06/04/99
M.H. Chiang, J.Y. Lee, J.M. Huang

METHOD FOR FORMING HIGH PURITY
SILICON OXIDE FIELD OXIDE ISOLATION
REGION

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

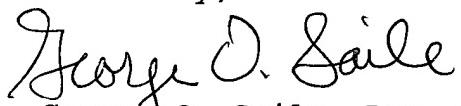
The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 5,151,381 to Liu et al., "Method for Local
Oxidation of Silicon Employing Two Oxidation Steps", discloses
a method for forming field isolation silicon oxide layers which
reduces or eliminates localized defects known as ribbons.

U.S. Patent 5,554,560 to Hsue et al., "Method for Forming a Planar Field Oxide (FOX) on Substrates for Integrated Circuit", discloses a method for forming planar silicon oxide field oxide (FOX) isolation layers with improved resistance to formation of localized stringer defects.

U.S. Patent 5,686,344 to Lee, "Device Isolation Method for Semiconductor Device", discloses a method for forming silicon oxide dielectric isolation regions within a silicon substrate in both the device isolation and well regions separating different polarities of silicon.

Sincerely,



George O. Saile, Reg. No. 19572